imall

Chipsmall Limited consists of a professional team with an average of over 10 year of expertise in the distribution of electronic components. Based in Hongkong, we have already established firm and mutual-benefit business relationships with customers from, Europe, America and south Asia, supplying obsolete and hard-to-find components to meet their specific needs.

With the principle of "Quality Parts, Customers Priority, Honest Operation, and Considerate Service", our business mainly focus on the distribution of electronic components. Line cards we deal with include Microchip, ALPS, ROHM, Xilinx, Pulse, ON, Everlight and Freescale. Main products comprise IC, Modules, Potentiometer, IC Socket, Relay, Connector. Our parts cover such applications as commercial, industrial, and automotives areas.

We are looking forward to setting up business relationship with you and hope to provide you with the best service and solution. Let us make a better world for our industry!



Contact us

Tel: +86-755-8981 8866 Fax: +86-755-8427 6832 Email & Skype: info@chipsmall.com Web: www.chipsmall.com Address: A1208, Overseas Decoration Building, #122 Zhenhua RD., Futian, Shenzhen, China







MMDT3904

DUAL NPN SMALL SIGNAL SURFACE MOUNT TRANSISTOR

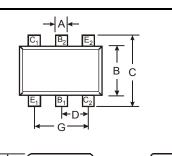
-55 to +150

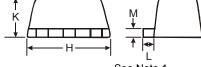
Features

- **Epitaxial Planar Die Construction**
- Ideal for Low Power Amplification and Switching
- Ultra-Small Surface Mount Package
- Lead Free By Design/RoHS Compliant (Note 3)
- "Green" Device (Note 4 and 5)

Mechanical Data

- Case: SOT-563
- Case Material: Molded Plastic. UL Flammability • Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020C
- Terminals: Finish Matte Tin annealed over Alloy 42 leadframe. Solderable per MIL-STD-202, Method 208
- Terminal Connections: See Diagram
- Terminals: Lead bearing terminal plating available. See Ordering information Page 3
- Marking Information: KAP, See Page 3
- Ordering Information: See Page 3
- Weight: 0.003 grams (approximate)







SOT-563									
Dim	Min	Мах	Тур						
Α	0.15	0.30	0.25						
в	1.10	1.25	1.20						
С	1.55	1.70	1.60						
D	0.50								
G	0.90	1.10	1.00						
Н	1.50	1.70	1.60						
κ	0.56	0.60							
L	0.10	0.30	0.20						
М	M 0.10		0.11						
All Dimensions in mm									

Maximum Ratings @T _A = 25°C unless otherwise specified								
Characteristic	Symbol	Value	Unit					
Collector-Base Voltage	V _{CBO}	60	V					
Collector-Emitter Voltage	V _{CEO}	40	V					
Emitter-Base Voltage	V _{EBO}	6.0	V					
Collector Current - Continuous	lc	200	mA					
Power Dissipation (Note	e 2) Pd	200	mW					
Thermal Resistance, Junction to Ambient	R _{0JA}	625	°C/W					

1. Package is non-polarized. Parts may be on reel in orientation illustrated, 180° rotated, or mixed (both ways).

Device mounted on FR-4 PCB, 1 inch x 0.85 inch x 0.062 inch; pad layout as shown on Diodes Inc. suggested pad layout document AP02001, which can be found on our website at http://www.diodes.com/datasheets/ap02001.pdf. 2.

T_j, T_{STG}

3. No purposefully added lead.

Operating and Storage Temperature Range

Notes:

4.

Diodes Inc.'s "Green" policy can be found on our website at http://www.diodes.com/products/lead_free/index.php. Product manufactured with Date Code UO (week 40, 2007) and newer are built with Green Molding Compound. Product manufactured prior to Date 5. Code UO are built with Non-Green Molding Compound and may contain Halogens or Sb2O3 Fire Retardants.

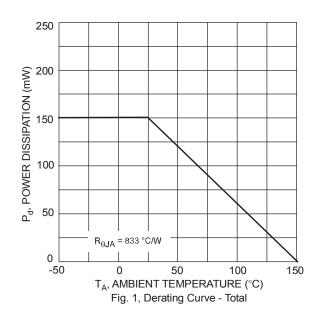
°C

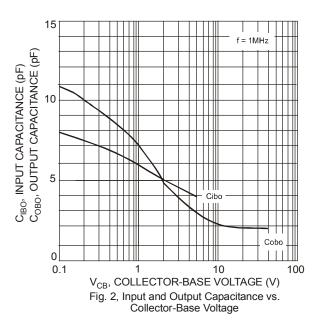


Electrical Characteristics @T_A = 25°C unless otherwise specified

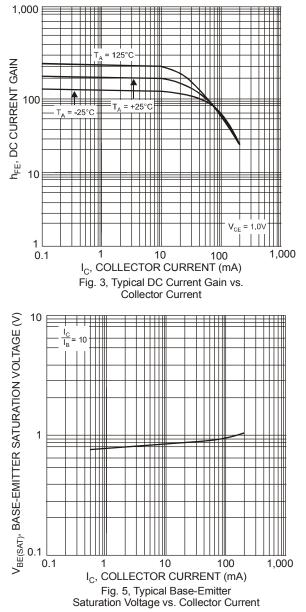
Characteristic	Symbol	Min	Max	Unit	Test Condition			
OFF CHARACTERISTICS (Note 6)	·							
Collector-Base Breakdown Voltage	V _{(BR)CBO}	60	_	V	$I_{\rm C} = 10 \mu {\rm A}, \ I_{\rm E} = 0$			
Collector-Emitter Breakdown Voltage	V _{(BR)CEO}	40		V	I _C = 1.0mA, I _B = 0			
Emitter-Base Breakdown Voltage	V _{(BR)EBO}	5.0		V	$I_{\rm E} = 10 \mu A, I_{\rm C} = 0$			
Collector Cutoff Current	I _{CEX}	_	50	nA	$V_{CE} = 30V, V_{EB(OFF)} = 3.0V$			
Base Cutoff Current	I _{BL}		50	nA	V _{CE} = 30V, V _{EB(OFF)} = 3.0V			
ON CHARACTERISTICS (Note 6)								
DC Current Gain	h _{FE}	40 70 100 60 30	 300 	_	$\begin{split} I_{C} &= 100 \mu A, \ V_{CE} &= 1.0 V \\ I_{C} &= 1.0 m A, \ V_{CE} &= 1.0 V \\ I_{C} &= 10 m A, \ V_{CE} &= 1.0 V \\ I_{C} &= 50 m A, \ V_{CE} &= 1.0 V \\ I_{C} &= 100 m A, \ V_{CE} &= 1.0 V \end{split}$			
Collector-Emitter Saturation Voltage	V _{CE(SAT)}	_	0.20 0.30	V	I_{C} = 10mA, I_{B} = 1.0mA I_{C} = 50mA, I_{B} = 5.0mA			
Base-Emitter Saturation Voltage	V _{BE(SAT)}	0.65	0.85 0.95	V	I_{C} = 10mA, I_{B} = 1.0mA I_{C} = 50mA, I_{B} = 5.0mA			
SMALL SIGNAL CHARACTERISTICS		-						
Output Capacitance	C _{obo}		4.0	pF	V_{CB} = 5.0V, f = 1.0MHz, I _E = 0			
Input Capacitance	Cibo		8.0	pF	V_{EB} = 0.5V, f = 1.0MHz, I _C = 0			
Input Impedance	h _{ie}	1.0	10	kΩ				
Voltage Feedback Ratio	h _{re}	0.5	8.0	x 10 ⁻⁴	V _{CE} = 10V, I _C = 1.0mA,			
Small Signal Current Gain	h _{fe}	100	400		f = 1.0kHz			
Output Admittance	h _{oe}	1.0	40	μS				
Current Gain-Bandwidth Product	f _T	300	—	MHz	V _{CE} = 20V, I _C = 10mA, f = 100MHz			
Noise Figure	NF	_	5.0	dB	V_{CE} = 5.0V, I _C = 100µA, R _S = 1.0kΩ, f = 1.0kHz			
SWITCHING CHARACTERISTICS								
Delay Time	t _d	—	35	ns	V _{CC} = 3.0V, I _C = 10mA,			
Rise Time	tr	_	35	ns	$V_{BE(off)}$ = - 0.5V, I_{B1} = 1.0mA			
Storage Time	ts		200	ns	V _{CC} = 3.0V, I _C = 10mA,			
Fall Time	t _f	_	50	ns	$I_{B1} = I_{B2} = 1.0 \text{mA}$			

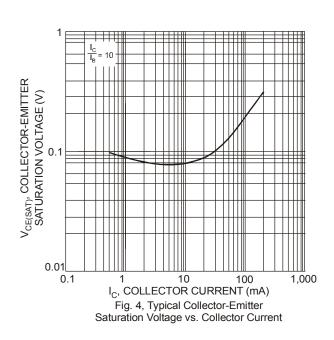
Notes: 6. Short duration pulse test used to minimize self-heating effect.











Ordering Information (Note 7)

Device	Packaging	Shipping
MMDT3904V-7	SOT-563	3000/Tape & Reel

Notes: 7. For packaging details, go to our website at http://www.diodes.com/datasheets/ap02007.pdf.

Marking Information

Date Code Kev				<u> П [</u> кар үм	Y Y	M = Date = Year (e	Code Mar ex: R = 200		ode			
Year	2004	20	05	2006	2007	20	08	2009	2010	20	011	2012
Code	R	S	6	T U		,	V	W	Х		Y	Z
Month	Jan	Feb	Mar	Apr	Мау	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	0	N	D



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